





**Electric-field control of interfacial in-plane magnetic anisotropy in CoFeB/MgO junctions**

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Magnetolectric coupling in metal/oxide heterostructures has opened up the possibility of controlling magnetization by voltage, i.e., electric field. However, the electric-field excitation of magnetization dynamics in perfectly in-plane and out-of-plane magnetized films have not been demonstrated so far due to zero electric-field torque originating from voltage control of perpendicular magnetic anisotropy. This limits the application of voltage-controlled magnetic anisotropy in magnetic field free control of magnetization dynamics. Here we show that magnetic annealing can induce an interfacial in-plane magnetic anisotropy of CoFeB/MgO junctions, thereby controlling the symmetry of interfacial magnetic anisotropy. The magnetic anisotropy is modulated by applying voltage: a negative bias voltage increases perpendicular magnetic anisotropy, while a positive bias voltage decreases perpendicular magnetic anisotropy and increases the in-plane magnetic anisotropy. Such a control of symmetry of the interfacial magnetic anisotropy by magnetic annealing and its tunability by electric fields is useful for developing purely voltage-controlled spintronic devices.

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**I. INTRODUCTION**

Recent discoveries such as spin-transfer torque, spin-orbit torque, and electric-field torque provide a new strategy for designing future spintronic devices which require power-efficient excitation of magnetization dynamics. In this regard, spin-transfer torque has been mainly utilized for exciting the magnetization dynamics in magnetic nanostructures [1,2]. However, there is an inevitable effect of Joule heating because of a high charge current density of  $\sim 10^{11}$  A/m<sup>2</sup> in the devices. Spin-orbit torques generated at an interface between nonmagnetic metals with strong spin-orbit interaction and ferromagnetic metals could be a promising approach for energy-efficient manipulation [3,4], yet recently reported charge current densities required for magnetization switching or exciting spin waves remain too large to be ignored [5,6]. Further significant reduction of power consumption is envisaged by voltage-controlled magnetic anisotropy (VCMA), wherein electric fields can be used to control magnetization [7].

The effect of an electric field on magnetic properties has been reported for various systems such as magnetic semiconductors, multiferroic materials, and magnetic metal/oxide bilayers [8]. In particular, CoFeB/MgO junctions have attracted much attention because of their great potential to realize ultralow power spintronic nanodevices, thanks to their giant

tunneling magnetoresistance [9,10] and strong perpendicular magnetic anisotropy (PMA) [11]. The magnetolectric coupling at the CoFeB/MgO interface allows us to control magnetization dynamics, such as ferromagnetic resonance (FMR) excitation, magnetization switching and spin-wave excitation, by using electric fields [7,12–17]. One mechanism to explain the electric-field effect is that magnetic anisotropy energy is changed by selective electron-hole doping into  $3d$  orbitals of the interfacial ferromagnetic atoms through spin-orbit interaction [18,19]. This interfacial PMA shows uniaxial symmetry where its energy is expressed in the form of  $K_{u\perp}\sin^2\theta$ , with  $K_{u\perp}$  being the uniaxial PMA energy and  $\theta$  being the elevation angle of the magnetization from the film plane. The corresponding electric-field torque caused by VCMA is estimated to be a function of  $\sin\theta\cos\theta$  obtained from the derivative of the energy terms. Therefore, VCMA experiments have so far used an external magnetic field for titling the magnetization direction, because electric-field torque is zero in the in-plane ( $\theta = 0^\circ$ ) or out-of-plane ( $\theta = 90^\circ$ ) magnetized samples [7]. However, a nonzero electric-field torque can be expected for the in-plane magnetized films if the interfacial magnetic anisotropy has an in-plane uniaxial component  $K_{u\parallel}$ , which is expressed in the form  $K_{u\parallel}\cos^2\theta\cos^2\phi$ ,  $\phi$  being the azimuthal angle. Such a modification of the electric-field torque offers an interesting opportunity to explore purely voltage-controlled spintronic devices. VCMA of in-plane magnetic anisotropy is reported for semiconducting (Ga,Mn)As thin films [20] and Fe/ $n$ -GaAs Schottky junctions [21]. There is so far no report about the interfacial in-plane magnetic anisotropy for CoFeB/MgO junctions.

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In this paper, we demonstrate that magnetic annealing can be utilized not only to enhance the typical PMA of CoFeB/MgO junctions but also to induce an in-plane magnetic anisotropy (IMA). First we describe the process of estimating the magnetic anisotropy fields. Then, using the obtained expression we quantify the effect of magnetic annealing on the magnetic anisotropy fields. Subsequently, we demonstrate that temperature dependence of both PMA and IMA can follow a power law of its saturation magnetization with an exponent of  $\sim 2$ , implying an interfacial origin. Finally, we present the electric-field effect on magnetic anisotropy fields using electrical detection of FMR. The VCMA behavior is clearly observed for both PMA and IMA at room temperature.

## II. ESTIMATION OF MAGNETIC ANISOTROPY FIELDS

The derivation of a relationship between a resonant magnetic field of FMR and azimuthal angle of the magnetization for an in-plane magnetized film, used for the estimation of magnetic anisotropy field of PMA and IMA, is described in this section. Let us consider that the direction of the magnetization  $M$  and external magnetic field  $H_{\text{ex}}$  is given by  $(\phi, \theta)$  and  $(\alpha, \beta)$ , respectively, where  $\alpha$  and  $\phi$  are the azimuthal angles and  $\beta$  and  $\theta$  are the elevation angles from the film plane. The magnetic free energy  $F$  can be expressed as a sum of the Zeeman energy, demagnetization energy, and magnetic anisotropy energy as below:

$$F = \frac{\mu_0 M_s}{2} [-2H_{\text{ex}}(\cos \theta \cos \beta \cos(\alpha - \phi) + \sin \theta \sin \beta) + (M_s - H_p)\sin^2 \theta - H_k \cos^2 \phi \cos^2 \theta], \quad (1)$$

where  $H_k$  is the in-plane anisotropy field directed along  $\phi = \theta = 0^\circ$ , and  $H_p$  is the perpendicular magnetic anisotropy field along  $\theta = 90^\circ$ .

Next we substitute  $F$  in the Smit-Beljers relation [22] given by

$$\left(\frac{f}{\gamma}\right)^2 = [M_s \cos \theta]^{-2} \left[ \frac{\partial^2 F}{\partial \theta^2} \frac{\partial^2 F}{\partial \phi^2} - \left( \frac{\partial^2 F}{\partial \theta \partial \phi} \right)^2 \right], \quad (2)$$

where  $f$  is the frequency and  $\gamma$  is the gyromagnetic ratio. We can obtain the free energy differentials with respect to  $\phi$  and  $\theta$  as follows:

$$\frac{\partial^2 F}{\partial \theta^2} = \mu_0 M_s [-H_{\text{ex}}(-\sin \theta \sin \beta - \cos \beta \cos(\alpha - \phi) \cos \theta) - (M_s - H_p) \cos 2\theta - H_k \cos^2 \phi \sin 2\theta], \quad (3)$$

$$\frac{\partial^2 F}{\partial \phi^2} = \mu_0 M_s [H_{\text{ex}}(\cos \theta \cos \beta \cos(\alpha - \phi)) + H_k \cos^2 \theta \cos 2\phi], \quad (4)$$

$$\frac{\partial^2 F}{\partial \theta \partial \phi} = -\mu_0 M_s \left[ H_{\text{ex}}(\sin \theta \cos \beta \sin(\alpha - \phi)) + \frac{H_k}{2} \sin 2\theta \sin 2\phi \right]. \quad (5)$$

In this study, FMR measurements were performed for in-plane magnetized films with the condition that  $M$  is parallel to  $H_{\text{ex}}$  in order to determine  $H_p$  and  $H_k$ . Using  $\theta = \beta = 0^\circ$  and  $\phi = \alpha$  in Eqs. (3)–(5) and substituting the resulting expressions in Eq. (2), we obtain

$$\left(\frac{f}{\gamma}\right)^2 = \frac{1}{M_s^2} [\mu_0 M_s H_{\text{ex}} + \mu_0 M_s (M_s - H_p) + \mu_0 M_s H_k \cos^2 \phi] [\mu_0 M_s H_{\text{ex}} + \mu_0 M_s H_k \cos 2\phi]. \quad (6)$$

Replacing  $H_{\text{ex}}$  with the term of resonant magnetic field  $H_{\text{res}}$  in Eq. (6), we obtain the relation between  $H_{\text{res}}$  and  $\phi$  as follows:

$$H_{\text{res}} = -H_k + \frac{3}{2} H_k \sin^2 \phi - \frac{(M_s - H_p)}{2} + \frac{1}{2} \left[ H_k^2 \sin^4 \phi + (M_s - H_p)^2 + 2(M_s - H_p) H_k \sin^2 \phi + 4 \left( \frac{f}{\mu_0 \gamma} \right)^2 \right]^{\frac{1}{2}}. \quad (7)$$

## III. EXPERIMENTAL DETAILS

Multilayer stacks of Ta(5)/Ru(10)/Ta(5)/Co<sub>20</sub>Fe<sub>60</sub>B<sub>20</sub>( $t$ )/MgO(2)/Al<sub>2</sub>O<sub>3</sub>(10) were sputtered at room temperature onto thermally oxidized Si(100) substrates at a base pressure of  $\sim 1 \times 10^{-7}$  Pa. The nominal thicknesses of each layer mentioned in the parentheses are in nanometers. The Al<sub>2</sub>O<sub>3</sub> layer serves as a capping layer to maintain the quality of the MgO layer, which is very important for interfacial magnetic anisotropy. Samples were annealed at a vacuum level of  $\sim 1 \times 10^{-3}$  Pa at different temperatures ranging from 100 °C to 400 °C in the presence of a bias magnetic field  $\mu_0 H_b = 500$  mT. The magnetization versus external magnetic

field ( $M$ - $H$ ) curves were measured by a superconducting quantum interference device (SQUID) magnetometer. The saturation magnetization  $M_s$  was measured for the samples annealed at different temperatures up to 600 °C.  $M_s$  was found to be constant at 1.5 T up to 400 °C, beyond which it drastically reduced to 450 mT. Such a decrease in the  $M_s$  is expected to arise from the interdiffusion of the ultrathin ferromagnetic layer, with a heavy metal underlayer at high annealing temperatures [23].

Broadband FMR measurements were used to estimate the magnetic anisotropy of samples. The sample was cut into pieces of size  $< 2 \times 2$  mm<sup>2</sup> and then placed face down on a coplanar waveguide (CPW) as shown in Fig. 1(a). The

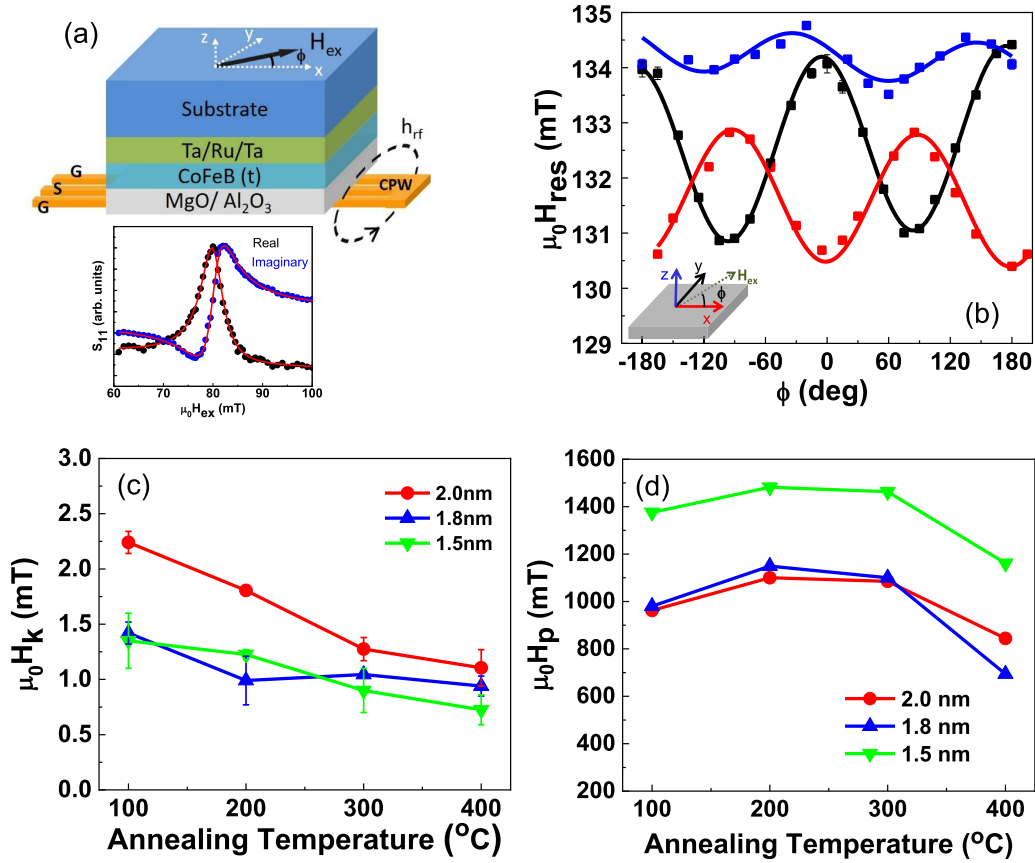


FIG. 1. (a) Schematic of the experimental setup used to detect FMR signal depicting the axes, ground (G) and signal (S) terminals of the coplanar waveguide (CPW) and the direction of the applied microwave field  $h_{rf}$ . Below a typical FMR spectra is shown that consists of imaginary and real parts of reflection parameter  $S_{11}$  (symbols) with fits to Eq. (8) (line). (b) In-plane angle  $\phi$  dependence of the resonant field  $H_{res}$  (squares) at frequency  $f = 8.0$  GHz for a 2.0-nm-thick CoFeB layer annealed at 200 °C in the presence of a magnetic field  $H_b$  along three orthogonal directions (arrows of corresponding color on the block in inset). Lines are fits to Eq. (7). (c) In-plane magnetic anisotropy field  $H_k$  plotted (solid symbols) as a function of annealing temperature for CoFeB layers with thicknesses ranging from 1.5 to 2.0 nm. (d) Corresponding perpendicular magnetic anisotropy  $H_p$  for the samples. Error bars represent the maximum deviation of the anisotropy fields obtained for different frequencies from the average value.

end of the CPW was connected to the port of a vector network analyzer and then a microwave field  $h_{rf}$  was applied to the samples by electromagnetic induction coupling. The reflection parameter ( $S_{11}$ ) was measured at fixed microwave frequency by varying an in-plane external magnetic field.

For the electrical detection of FMR using spin pumping and inverse spin Hall effect (ISHE) measurements, the multilayer structure was first patterned into a rectangular shape with dimensions  $10 \times 200 \mu\text{m}^2$  by using photolithography and Ar-ion milling. The bottom electrodes for detecting ISHE voltage from the Ta layer underneath the CoFeB layer and the top electrode on the  $\text{Al}_2\text{O}_3$  layer for applying voltage were fabricated by lift-off processes. Finally, a 200-nm-thick Ti/Au CPW for the application of a microwave magnetic field was deposited adjacent to the multilayer structure with the rectangular shape. The amplitude of the microwave signal was modulated with a frequency of 79 Hz, and then ISHE voltage was detected by a standard lock-in technique across the bottom electrodes in the Ta layer.

## IV. RESULTS AND DISCUSSION

### A. Effect of magnetic annealing on magnetic anisotropy

An example of the real and imaginary parts of the  $S_{11}$  parameter recorded in the FMR measurement is shown below the setup in Fig. 1(a). The obtained data are fitted by

$$S_{11} = \frac{L \times dH^2}{(H_{ex} - H_{res})^2 + dH^2} + \frac{D \times dH \times (H_{ex} - H_{res})}{(H_{ex} - H_{res})^2 + dH^2} + a \times H_{ex} + b, \quad (8)$$

where  $L$  and  $D$  are the weights of the Lorentzian and dispersive parts, respectively,  $dH$  is the half-width at half maximum, and  $a$  and  $b$  are constants. In case of a sample with 2.0-nm-thick CoFeB layer annealed at 200 °C in the presence of  $\mu_0 H_b = 500$  mT perpendicular to the film plane,  $\mu_0 H_{res} = 80.3$  mT is obtained at the microwave frequency  $f = 6.0$  GHz.

Subsequently, we study the effect of  $H_b$  on magnetic anisotropy of the samples. For comparison, we first measure

the in-plane angular dependence of  $H_{\text{res}}$  of the films prior to annealing, from which we can obtain  $\mu_0 H_k$  and  $\mu_0 H_p$  as 1.0 and 966 mT, respectively. Such an in-plane anisotropy typically appears in random directions during the deposition process. When the films are annealed in the presence of  $H_b$  in an in-plane direction which is perpendicular to the *inherent* in-plane magnetic anisotropy ( $x$  axis), we observe minima along  $\phi = 0^\circ$  in the  $H_{\text{res}}$  vs  $\phi$  plots as shown (red) in Fig. 1(b). On the other hand, if we anneal the films with  $H_b$  parallel to the *inherent* anisotropy of the films ( $y$  axis), we can see a 90-degree phase difference between  $x$  and  $y$ -axial annealing. Meanwhile, if we anneal the films with  $H_b$  perpendicular to the sample plane ( $z$  axis), the amplitude of the sinusoidal behavior for  $H_{\text{res}}$  vs  $\phi$  is clearly suppressed (blue). Upon fitting the experimental data in Fig. 1(b) using Eq. (7), we can obtain  $\mu_0 H_k$  and  $\mu_0 H_p$  as 1.3 and 1083 mT, 1.8 and 1088 mT, 0.4 and 1096 mT for the  $x$ -,  $y$ -, and  $z$ -axis magnetic annealing, respectively. The small in-plane component for perpendicular  $H_b$  and the different magnitude of the anisotropy field between the  $x$ - and  $y$ -axis magnetic fields may be due to the misalignment in the experimental setup during the annealing.

In order to see the effect of annealing temperature on magnetic anisotropies, we measure the  $H_k$  and  $H_p$  as shown in Figs. 1(c) and 1(d), respectively, for different CoFeB thicknesses of 1.5, 1.8, and 2.0 nm. Please note that  $H_k$  in all the samples were induced by annealing. It is observed that  $H_k$  for all the thicknesses decreases with increasing annealing temperature. On the other hand,  $H_p$  increases with increasing annealing temperature, reaching to a maximum at around 300 °C, and then drastically decreases with the further increment of annealing temperature because of intermixing of the interface, as reported in previous studies [23,24]. There have been many experimental and theoretical studies on IMA induced by magnetic annealing for bulk samples. The easy axis of the IMA is parallel to the direction of an external magnetic field during annealing. One plausible model to explain its mechanism in a cubic lattice such as NiFe and CoFe is directional ordering of atomic pairs: in alloys consisting of A and B atoms, an anisotropic distribution of different atom pairs such as AA, BB, and AB yields a uniaxial anisotropy [25–28]. In this study,  $H_k$  decreases with increasing annealing temperature, because migration of atoms causes an isotropic distribution of atom pairs among Co, Fe, and B. Higher temperature annealing leads to improved crystallinity as well as atomic order at the CoFeB/MgO interface [29], and therefore  $H_p$  is enhanced as shown in Fig. 1(d).

### B. Temperature dependence of magnetization and magnetic anisotropy

The temperature dependence of saturation magnetization  $M_s(T)$  was measured using SQUID. The corresponding data for the 2.0-nm-thick CoFeB layer annealed at 200 °C is shown in Fig. 2(a). The monotonic change with respect to temperature implies that the annealing process does not give rise to any oxide interlayer in the CoFeB/MgO junctions [30]. A decrease in the saturation magnetization at higher temperatures is due to the increment of thermal fluctuations and excitation of spin-wave modes that tend to destabilize the orientation of magnetic moments. The experimental data were fitted using

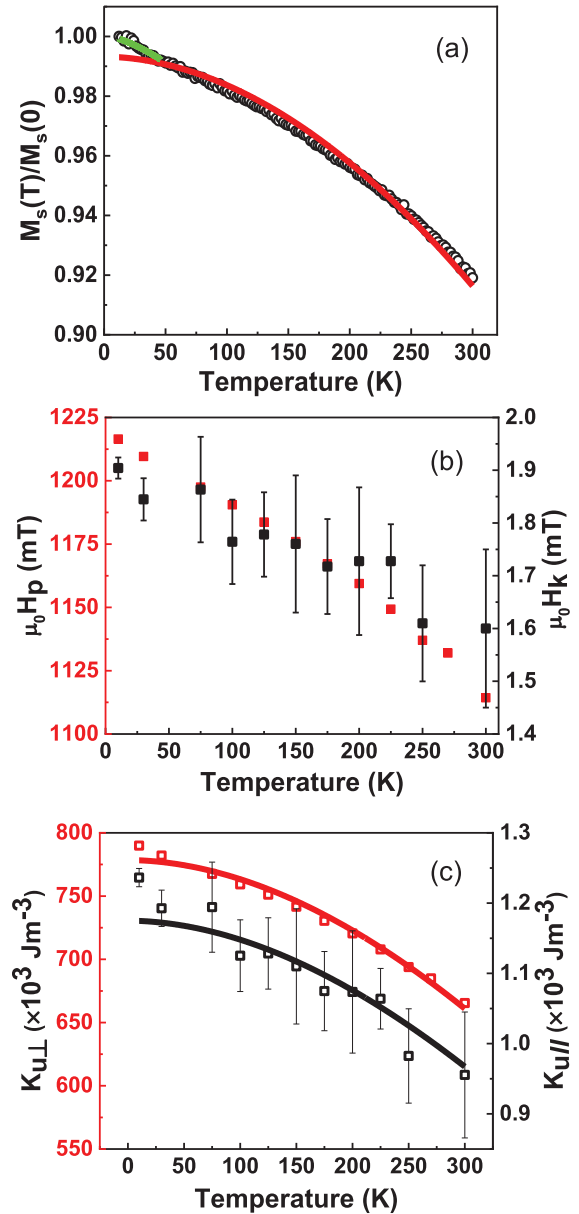


FIG. 2. (a) Saturation magnetization  $M_s$  as a function of temperature. Upon fitting using Bloch's law,  $T_C = 1150$  K and  $\chi = 1.5$  is obtained for  $T < 50$  K (green line) and  $T_C = 1150$  K and  $\chi = 1.8$  for  $T > 50$  K (red line). (b) Temperature dependence of anisotropy fields  $H_p$  (red squares) and  $H_k$  (black squares). (c) Anisotropy energies  $K_{u\perp}$  (red squares) and  $K_{u\parallel}$  (black squares) corresponding to  $H_p$  and  $H_k$  are plotted as a function of temperature. Lines are fits to power law of magnetization given by the Callen-Callen relation with  $\gamma = 2.1$  and 2.3 for  $K_{u\perp}$  and  $K_{u\parallel}$ . Error bars represent maximum deviation of the anisotropy fields and corresponding energies obtained for different frequencies from the average value.

Bloch's law  $M_s(T) = M_s(0)[1 - (\frac{T}{T_C})^\chi]$ , where  $T_C$  is the Curie temperature and  $\chi$  is Bloch's exponent. Up to  $T = 50$  K, the experimental data fits well to Bloch's law using  $T_C = 1150$  K and  $\chi = 1.5$ , as shown by the green line in Fig. 2(a). The data in the measurement range of 50–300 K was fitted to Bloch's law using  $T_C = 1150$  K and  $\chi = 1.8$ , as shown by the red line in the same figure. A difference in the exponents between

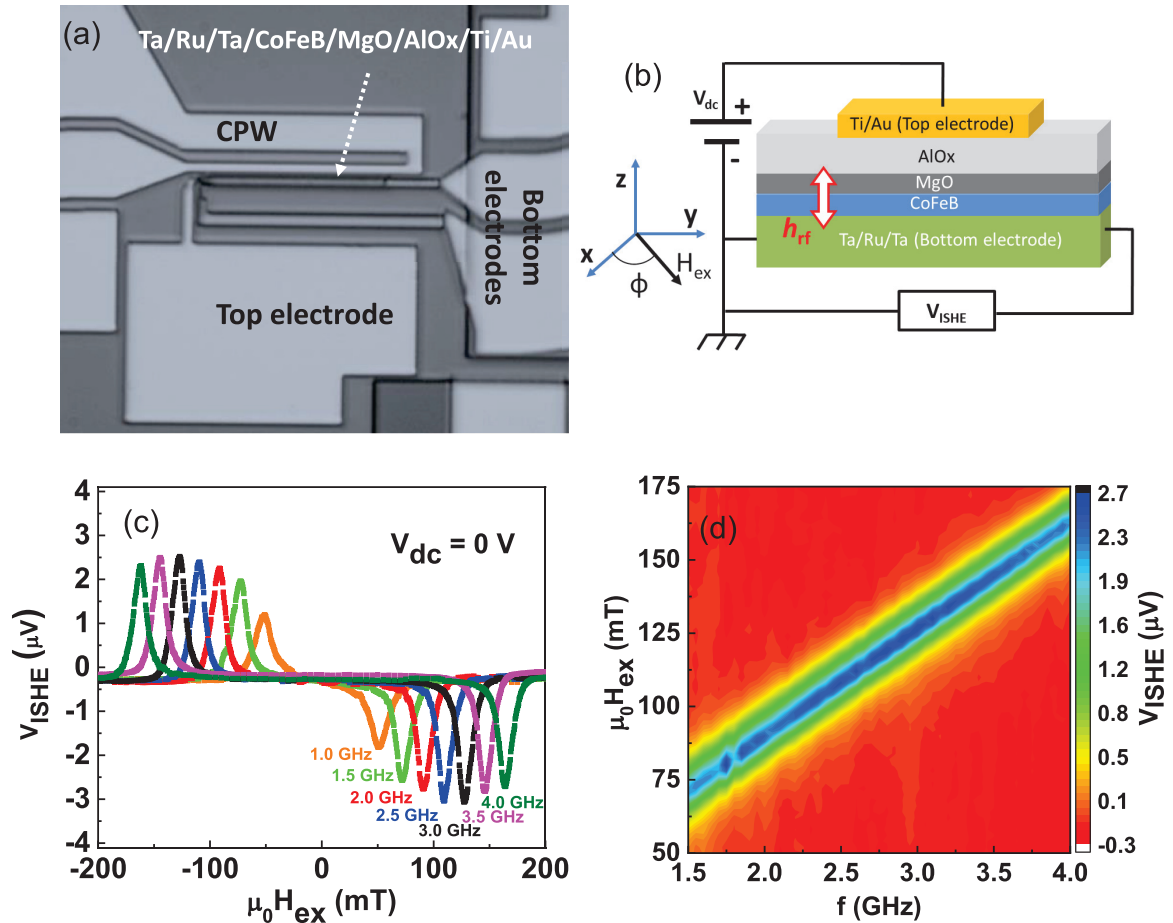


FIG. 3. (a) Optical microscope image of the device used for electrical detection of FMR under bias voltages. (b) Schematic of the experimental setup used to detect FMR signal electrically via spin pumping and inverse spin Hall effect (ISHE). Spin current generated from the CoFeB layer by spin pumping is converted into a charge current due to ISHE of Ta and then gives rise to a rectified voltage  $V_{\text{ISHE}}$ . The Ti/Au top electrode allows us to apply a bias voltage  $V_{\text{dc}}$  at the CoFeB/MgO interface. (c) External magnetic field  $H_{\text{ex}}$  dependence of  $V_{\text{ISHE}}$  at different frequencies  $f$ . (d) Color-coded  $V_{\text{ISHE}}$  spectra.

lower and higher measurement temperatures can be expected due to the magnon-magnon scattering [31].

The temperature dependence of anisotropy fields,  $H_p$  and  $H_k$ , of the corresponding sample were estimated using temperature-dependent FMR measurements. Both  $H_p$  and  $H_k$  are found to be increased monotonically with decreasing temperature, as shown in Fig. 2(b). Figure 2(c) shows the temperature dependence of the corresponding magnetic anisotropy energies. Since the dominant contribution to PMA in CoFeB/MgO junctions comes from the interface between the two layers, we can approximately equate  $K_i/t$ ,  $K_i$  being the interfacial PMA, to the energy corresponding to the PMA field  $K_{u\perp}(T) = \frac{M_s(T)H_p(T)}{2}$  [32]. The experimental data are then fitted to the Callen-Callen power law of the magnetization [33], which can be written as  $\frac{K_{u\perp}(T)}{K_{u\perp}(0)} = \left(\frac{M_s(T)}{M_s(0)}\right)^\gamma$ , using the scaling exponent  $\gamma = 2.1$ . According to the Callen-Callen model, the anisotropy energy scales as a function of temperature with  $\gamma = 3$  for a ferromagnet which has a single site origin of magnetic anisotropy. However, a scaling exponent of  $\gamma \sim 2$  has been observed in VCMA systems with interfacial magnetic anisotropies such as Ta/CoFeB/MgO [32,34,35] and Ru/Co<sub>2</sub>FeAl/MgO [36]. Such a deviation from the Callen-

Callen model is due to the presence of interfacial hybridization between the  $3d$  orbitals of Fe and  $2p$  orbitals of O atoms in the CoFeB/MgO junction. Upon estimating the energy corresponding to IMA  $K_{u\parallel}$  using a similar relation, as shown in Fig. 2(c), we are able to fit the temperature dependence of the anisotropy energies to the power law of magnetization using  $\gamma = 2.3$ . This indicates that, in addition to PMA, even IMA can have interfacial origin of the CoFeB/MgO junction.

### C. Electric-field control of interfacial magnetic anisotropy

We study the electric-field effect on  $H_k$  and  $H_p$  of the CoFeB/MgO junction via spin pumping and ISHE measurements. The optical microscope image of the device used in this process is shown in Fig. 3(a). The FMR signal was detected electrically by using ISHE as shown in Fig. 3(b). In this setup, the microwave magnetic field  $h_{\text{rf}}$  was applied perpendicular to the CoFeB layer from a nearby CPW. When FMR occurs, spin pumping generates spin current at the interface between CoFeB and Ta, and then the spin current is converted into charge current via ISHE in the Ta layer. Figure 3(c) shows the detected ISHE voltage  $V_{\text{ISHE}}$  as a function of an external magnetic field  $H_{\text{ex}}$  for  $f$  from 1.0 to 4.0 GHz. The  $V_{\text{ISHE}}$  signal

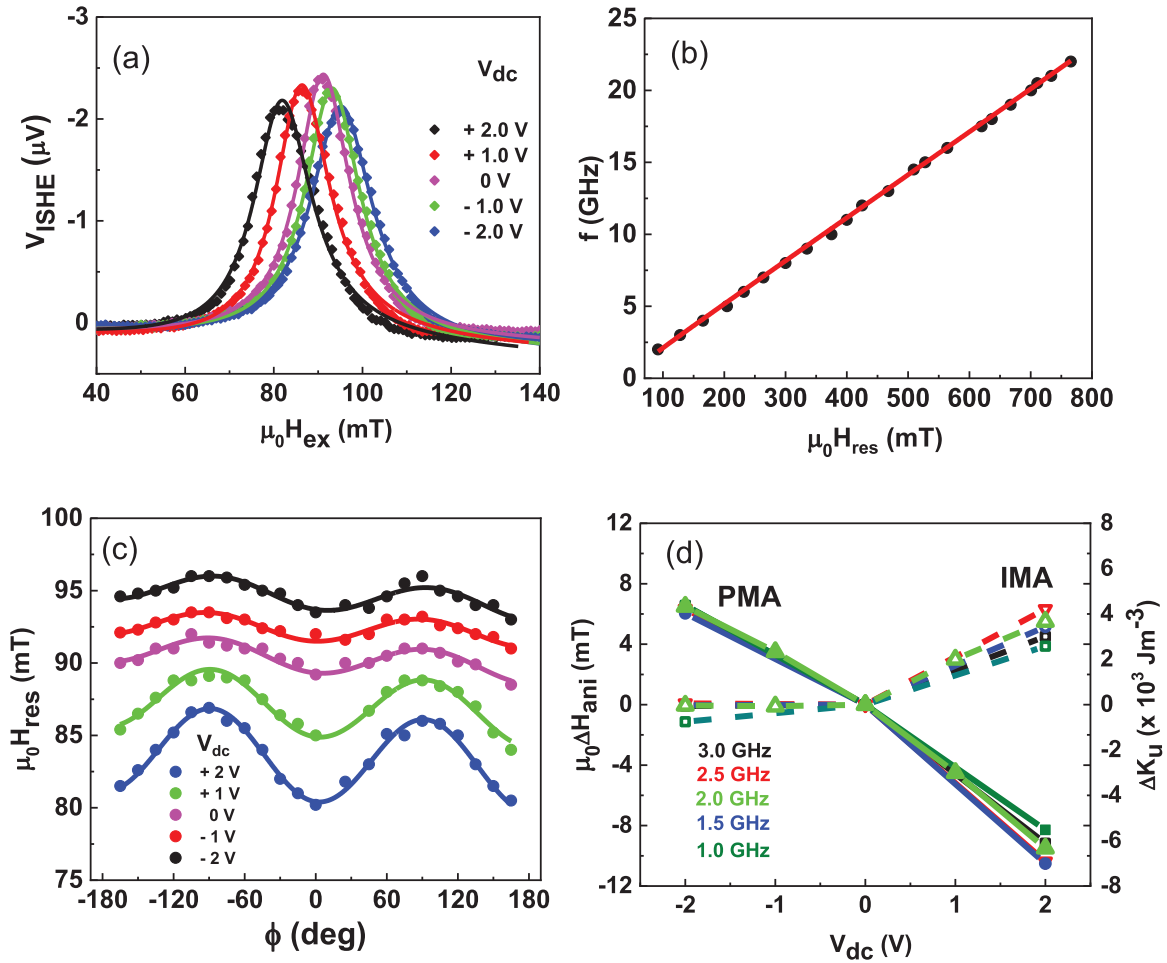


FIG. 4. (a) Dependence of  $V_{ISHE}$  spectra on bias voltage  $V_{dc}$  at frequency  $f = 2.0$  GHz (symbols). The lines are fits to experimental data by using Eq. (8). (b) Resonance fields  $H_{res}$  as a function of  $f$  (symbols) with fits to Eq. (9). (c) In-plane angle  $\phi$  dependence of  $H_{res}$  at different  $V_{dc}$  at  $f = 2.0$  GHz. The lines are fits to experimental data using Eq. (7). (d) The change of anisotropy fields  $\mu_0 \Delta H_{ani}$  (symbols with lines) with respect to  $V_{dc}$  is shown on the left while the corresponding change in energies  $\Delta K_u$  is shown on the right axis. PMA and IMA refer to perpendicular and in-plane magnetic anisotropy, respectively.

shows the sign reversal with respect to the direction of  $H_{ex}$ , implying inverse spin Hall effect origin of measured signals.

It is reported that the line shape of the rectification voltage in spin pumping measurements strongly depends upon the microwave magnetic field distribution in the sample and contributions from anomalous Hall effect (AHE) or anisotropic magnetoresistance (AMR) [37]. According to Harder *et al.*, in this setup, AHE and AMR of the ferromagnet show dispersive and Lorentzian lineshape, respectively, and ISHE shows Lorentzian lineshape. However, the AMR and ISHE spectra amplitudes show angular-dependent behavior of the types  $\sin 2\phi$  and  $\sin \phi$ , respectively. An angular-dependent measurement in our devices revealed purely Lorentzian line shape of  $V_{ISHE}$  spectra whose amplitude has a  $\sin \phi$  dependence. This confirms that the rectified voltage originates from an inverse spin Hall effect where the FMR is excited by a  $z$ -axial microwave field. The magnitude of the rectification voltage in the spectra increases with increasing frequency up to 3.0 GHz and then starts to decrease with the further increase of frequency. This behavior is due to the fact that the spin current increases with increasing frequency for the spin pumping mechanism,

but the increase of  $H_{ex}$  during FMR decreases the cone angle of magnetization precession, and therefore the generation of the spin current is suppressed at high frequencies [38]. The dependence of  $V_{ISHE}$  on the microwave frequency and  $H_{ex}$  is plotted as a color map in Fig. 3(d). The resonant magnetic field increases monotonically with frequency, which is consistent with the Kittel formula.

DC bias voltage  $V_{dc}$  is applied in the sample, as shown in Fig. 3(b). The effect of  $V_{dc}$  on the ISHE spectra is plotted in Fig. 4(a). The resonant field  $\mu_0 H_{res}$  is monotonically changed from 80 to 94 mT by applying  $V_{dc}$ . In order to understand the origin of the change of  $H_{res}$  on  $V_{dc}$ , firstly, the gyromagnetic ratio  $\gamma$  in Eq. (7) is estimated. We used a process similar to a method described by Shaw *et al.* [39], which shows that the error in simultaneous estimation of the effective magnetization  $M_{eff}$  and gyromagnetic ratio from the Kittel equation can be minimized by recording the FMR spectra up to  $H_{ex}$  well above the  $M_{eff}$ . The FMR spectra was detected electrically with an in-plane  $\mu_0 H_{ex}$  up to 800 mT along  $\phi = 0^\circ$ .  $H_{res}$  obtained are plotted as a function of frequency as shown in Fig. 4(b). In case of  $\phi = 0^\circ$ , Eq. (7) reduces to the typical

form of Kittel equation as follows:

$$\begin{aligned} f &= \gamma \sqrt{(H_{\text{res}} + H_k - M_{\text{eff}})(H_{\text{res}} + H_k)} \\ &= \gamma \sqrt{(H_{\text{res}} - M_{\text{eff}})H_{\text{res}}}. \end{aligned} \quad (9)$$

The in-plane anisotropy can be assumed to be absent in this process, since its effect was found to be negligible for our purposes. We obtain  $M_{\text{eff}} = 50$  mT and  $\gamma = 0.0298$  GHz/mT from the fitting. Furthermore, we could not detect any effect of electric field on the gyromagnetic ratio in the applied bias voltage range.

Since the gyromagnetic ratio is found to be invariant with  $V_{\text{dc}}$ , secondly, the change of  $H_p$  and  $H_k$  on the application of  $V_{\text{dc}}$  is estimated. The  $V_{\text{ISHE}}$  spectra were measured as a function of in-plane magnetic field angle  $\phi$  at different bias voltages, as discussed in the previous paragraph. Surprisingly, the sinusoidal amplitude in the  $\phi$  dependence of  $H_{\text{res}}$ , as shown in Fig. 4(c), is strongly modulated by applying  $V_{\text{dc}}$ , implying voltage control for  $H_k$ . Upon fitting the experimental data using Eq. (7), it can be observed that  $H_p$  and  $H_k$  are controlled by bias voltage with a mutually opposite dependence on  $V_{\text{dc}}$ . Figure 4(d) shows the change of the anisotropy fields and the corresponding anisotropy energies on the left and right axes, respectively, as a function of  $V_{\text{dc}}$  with respect to the unbiased condition ( $V_{\text{dc}} = 0$  V) for frequencies from 1.0 to 3.0 GHz. When the top electrode is at a lower potential than the bottom CoFeB electrode (negative bias voltage),  $H_p$  is observed to increase, whereas  $H_k$  remains almost unchanged. On the other hand, a positive bias voltage decreases  $H_p$  and increases  $H_k$ .

The penetration depths of the electric field in metallic ferromagnets is about 0.1 nm and therefore the change of  $H_p$  and  $H_k$  with bias voltage suggests that PMA and IMA of the CoFeB/MgO junction are of interfacial origin. VCMA in ferromagnetic metal/oxide interface is understood by a relative change in electron density for the in-plane and out-of-plane oriented  $3d$  orbitals of the interfacial ferromagnetic atoms in the presence of an electric field [40]. The electron filling factor in the  $d_{z^2}$  orbital is reduced by applying a negative voltage, which leads to increase in PMA. On the other hand, when a positive voltage is applied, the electron filling factors in the out-of-plane and in-plane oriented  $3d$  orbitals are enhanced

and suppressed, respectively, leading to a decrease in PMA, accompanied by an increase in IMA. The asymmetric trend of VCMA with respect to the sign of voltage in the samples is predicted for buffer layer/ferromagnetic metal/oxide multilayers, which lack spatial inversion symmetry perpendicular to the film plane [41].

## V. CONCLUSION

In conclusion, in addition to typical perpendicular magnetic anisotropy of CoFeB/MgO junctions, an interfacial in-plane magnetic anisotropy is observed whose orientation can be controlled by the direction of applied magnetic field during annealing. Both in-plane and perpendicular magnetic anisotropies could be modulated by electric fields: a negative bias voltage increases perpendicular magnetic anisotropy, while a positive bias voltage decreases perpendicular magnetic anisotropy and increases the in-plane magnetic anisotropy. This behavior can be understood by a change of electron density for the in-plane and out-of-plane  $3d$  orbitals of the ferromagnetic atoms in the presence of electric field at the CoFeB/MgO junction. So far, the electric-field torque is reported for magnetization direction tilted away from the in-plane and out-of-plane direction of the sample with the application of bias magnetic field. However, our demonstration of voltage-controllable in-plane and perpendicular anisotropies of the CoFeB/MgO junction can overcome the requirement of such bias magnetic fields. We believe that such a control of symmetry of the magnetic anisotropy by magnetic annealing and its tunability by electric fields is a crucial development towards realizing purely voltage-controlled spintronic devices with ultralow power consumption.

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